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(71) Applicant: SONY CORP

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(54) THIN-FILM SEMICONDUCTOR DEVICE

(57) Abstract:

PROBLEM TO BE SOLVED: To rationalize the production process of a thin-film dual-gate transistor.

SOLUTION: The thin-film semiconductor device contains at least the thin-film transistor formed on a substrate 1. The transistor has the dual-gate structure which is composed of a semiconductor thin film 4 and a pair of gate electrodes 2F, 2R which are arranged in the upper part and the lower part of the film 4 via respective insulating films. The gate electrode 2R on one side is composed of a material whose transmissivity is at less than 1%. The gate electrode 2F on the other side is composed of a material whose transmissivity is at 1% or more.

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